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# Mechanical properties of Al<sub>4</sub>SiC<sub>4</sub> bulk ceramics produced by solid state reaction

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#### **Abstract**

The mechanical properties at ambient and high temperature of  $Al_4SiC_4$  bulk ceramics prepared by solid state reaction were investigated. By increasing the sintering temperature slightly, the room temperature bending strength increased up to 318 MPa, whereas, the fracture toughness decreased with the increase of the sintering temperatures. The high temperature bending strengths of the  $Al_4SiC_4$  ceramics exhibited anomalous increases within certain temperature ranges especially at 1300 °C in air with the highest value of 449.7 MPa, i.e. about 1.5 times of that at room temperature (300 MPa). The self-healing behavior of the flaws on the specimen surface due to the oxidation of the surface layer of the  $Al_4SiC_4$  ceramics is considered to be the main strength-enhancing mechanism at high temperatures.

Keywords: C. Mechanical properties; Al<sub>4</sub>SiC<sub>4</sub>; High temperature mechanical properties; Self-healing properties

### 1. Introduction

As one of the promising high-temperature ceramics, Al<sub>4</sub>SiC<sub>4</sub> has been under active development for demanding high temperature applications, special refractory materials and high-temperature structural materials for its unique combination of the high melting point (~2080 °C), the low density (3.03 g/cm<sup>3</sup>), excellent oxidation resistance and corrosion resistance [1-3]. Recently, some studies have been done on the synthesis of Al<sub>4</sub>SiC<sub>4</sub> powders and Al<sub>4</sub>SiC<sub>4</sub> bulk ceramics [4,5]. The oxidation behavior, physical properties and the electrical conductivities of this material were also studied [6–8]. However, the mechanical properties, especially the high temperature mechanical properties have not been extensively studied so far. Thus, in this study, the mechanical properties of Al<sub>4</sub>SiC<sub>4</sub> ceramics have been investigated, particularly the enhanced mechanism of fracture toughness at room temperature and the increased bending strength at high temperature in air.

## 2. Experimental procedure

The material used in this work is bulk  $Al_4SiC_4$  ceramics which were fabricated by the solid state reaction process according to the following procedure. The molar ratio of Al, graphite and SiC conversed from polycarbosilane (PCS) was 4:3:1 as required by Eq. (1):

$$4Al + 3C + SiC \rightarrow Al_4SiC_4 \tag{1}$$

The pre-mixed powders of Al and graphite were homogeneously dispersed in the PCS solution using a magnetic stirring apparatus for 20 min. The resulting slurry was gently heated to remove the solvent. Subsequently, the mixture was compacted under 10–20 MPa, and calcined in a tube furnace with flowing argon at 1100 °C for 60 min. The baked body was ball-milled into powders which were compacted in a graphite sleeve with BN coated in the inner wall, and hot pressed at different temperatures: 1700 °C for 2 h then at 1800 °C for 1 h (Al<sub>4</sub>SiC<sub>4</sub>1700), at 1800 °C for 2 h then at 1900 °C for 1 h (Al<sub>4</sub>SiC<sub>4</sub>1800) and 1900 °C for 2 h then at 2000 °C for 1 h (Al<sub>4</sub>SiC<sub>4</sub>1900), respectively, with the pressure of 25 MPa and under Ar. The specimens prepared by this process are almost pure and dense.

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Table 1 Mechanical properties of Al<sub>4</sub>SiC<sub>4</sub> ceramics at room and high temperatures

Specimen	Relative density (%)	Bending strength (MPa)	Fracture toughness (MPa m <sup>1/2</sup> )	High temperature bending strength (MPa)		
				1000 °C	1200 °C	1300 °C
Al <sub>4</sub> SiC <sub>4</sub> 1700	91.7	$240.3 \pm 11.4$	$4.23 \pm 0.02$			
Al <sub>4</sub> SiC <sub>4</sub> 1800 Al <sub>4</sub> SiC <sub>4</sub> 1900	95.3 97.4	$297.1 \pm 22.4$ $318.8 \pm 22.3$	$3.98 \pm 0.05$ $3.70 \pm 0.09$	$385.4 \pm 35.1$	$388.3 \pm 79.1$	$449.7 \pm 25.6$

The specimens parallel to the hot-pressing axis were cut to various sizes for mechanical tests. The room temperature and high temperature bending strength tests in air atmosphere or in vacuum were conducted by three point bending method using an Instron instrument. Specimens with dimensions of  $3 \text{ mm} \times 4 \text{ mm} \times 36 \text{ mm}$  (30 mm outer span) were cut by means of a diamond saw. After grinding on all sides, the tensile surfaces were polished to a 1 µm finish and the tensile edges were beveled. The specimens were loaded with a crosshead speed of 0.5 mm/min. The single-edge-notchedbeam (SENB) method was used for the fracture toughness measurement at room temperature on notched specimens of  $2 \text{ mm} \times 4 \text{ mm} \times 20 \text{ mm}$  (16 mm outer span), with a crosshead speed of 0.05 mm/min. The strength and fracture toughness data summarized in Table 1 are the mean values of six specimens. The density was measured by the Archimedes water-immersion technique. The microstructure and the surface of the testing specimens were observed using SEM and TEM, respectively.

### 3. Results and discussion

### 3.1. Microstructure

The typical microstructure of Al<sub>4</sub>SiC<sub>4</sub> ceramics is shown in Fig. 1. One of the most obvious microstructural characteristics

is that the Al<sub>4</sub>SiC<sub>4</sub> grains have different morphologies on the planes perpendicular and parallel to the hot-pressing axis, from which a plate-like morphology with straight edges of the Al<sub>4</sub>SiC<sub>4</sub> grains is shown clearly. The formation of plate-like morphology can be attributed to its hexagonal crystal structure testified by its SAED (see Fig. 1(b and d)) [9]. The length of these grains is 2–5  $\mu m$  (Fig. 1(a)) and the thicknesses of the Al<sub>4</sub>SiC<sub>4</sub> grains range about 1  $\mu m$  (Fig. 1(c)). Defects like stacking faults were observed by TEM in the Al<sub>4</sub>SiC<sub>4</sub> grains. Fig. 1(d) indicates that the stacking faults are parallel to the basal plane {0 0 0 1}.

# 3.2. Mechanical properties of $Al_4SiC_4$ ceramics at room temperature

The room temperature mechanical properties of this material including bending strength and fracture toughness are summarized in Table 1, and the corresponding curves of bending strength and fracture toughness versus sintering temperatures can be seen in Fig. 2. The bending strengths slightly increase with increasing sintering temperatures, which may be due to its favorable effect of the densification on these ceramics (as shown in Table 1). The room temperature bending strength of Al<sub>4</sub>SiC<sub>4</sub> ceramic reached the maximum value of 330 MPa for Al<sub>4</sub>SiC<sub>4</sub>1900. Surely this value is not very high compared with other ceramics; the reasonable explanation is

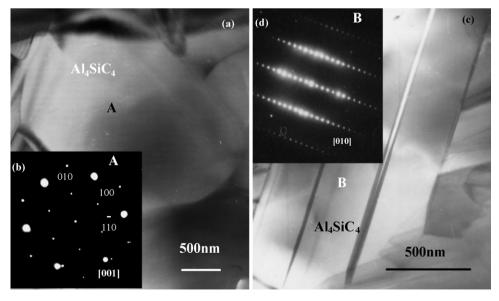


Fig. 1. TEM micrograph observation Al<sub>4</sub>SiC<sub>4</sub> 1800 ceramics. (a) Perpendicular to the hot-pressing axis, (b) corresponding SAED of area A; (c) parallel to the hot-pressing axis and (d) corresponding SAED of area B.

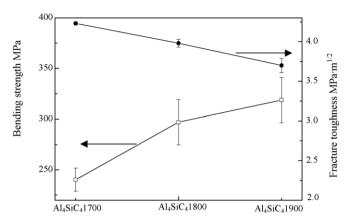


Fig. 2. Bending strengths and fracture toughness of Al<sub>4</sub>SiC<sub>4</sub> ceramics sintered at different temperatures.

that the Al<sub>4</sub>SiC<sub>4</sub> grains are more anisotropic, as shown in Fig. 1. So there must exist a high level of interfacial stresses between grains due to the difference between thermal expansions coefficients in different directions. With increasing sintering

temperatures, however, another remarkable aspect is that the fracture toughnesses of Al<sub>4</sub>SiC<sub>4</sub> ceramics continuously decreases. For Al<sub>4</sub>SiC<sub>4</sub> bulk ceramics, the toughness of Al<sub>4</sub>SiC<sub>4</sub>1700 is 4.2 MPa m<sup>1/2</sup> and that of Al<sub>4</sub>SiC<sub>4</sub>1900 is 3.70 MPa m<sup>1/2</sup>. A possible explanation will be discussed as follows.

The typical fracture surface of an Al<sub>4</sub>SiC<sub>4</sub> ceramic is shown in Fig. 3, which displays the mixed inter- and intra-granular fracture behavior. Some pull-out of the plate-like grains can also be observed in the Al<sub>4</sub>SiC<sub>4</sub>1700 specimen (labeled with arrows). Moreover, comparing with Al<sub>4</sub>SiC<sub>4</sub>1900, the intergranular fracture of the Al<sub>4</sub>SiC<sub>4</sub>1700 was often happened resulting from the weak interfacial bonding. Fig. 4(a–c) shows that graphite phases appear in the Al<sub>4</sub>SiC<sub>4</sub>1700 specimen at the interface of Al<sub>4</sub>SiC<sub>4</sub> grains. It has a thickness of 0.1–0.5 μm. Some microcracks occur around the graphite (Fig. 4(a)) or at the tip of the graphite (Fig. 4(b)) (labeled with arrows). Graphite phases shaped like a wedge have been observed. The intergranular fracture was often formed along the interfaces between Al<sub>4</sub>SiC<sub>4</sub> grains and carbon grains,

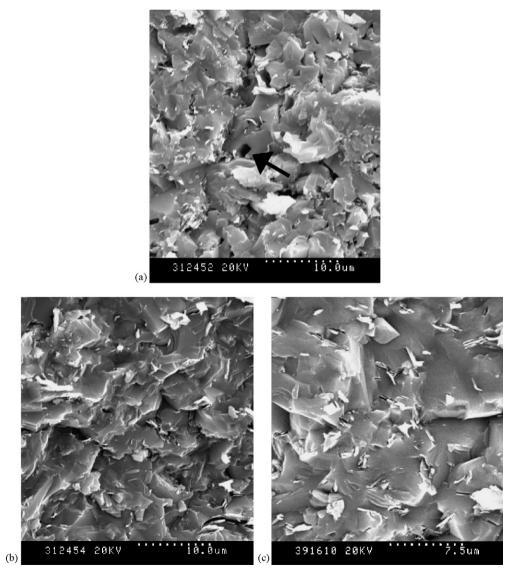
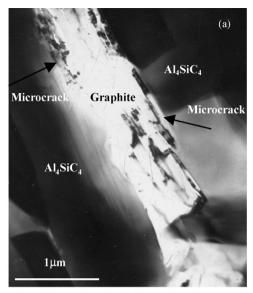


Fig. 3. Fracture surfaces of Al<sub>4</sub>SiC<sub>4</sub> ceramics sintered at different temperatures. (a) Al<sub>4</sub>SiC<sub>4</sub>1700; (b) Al<sub>4</sub>SiC<sub>4</sub>1800 and (c) Al<sub>4</sub>SiC<sub>4</sub>1900.



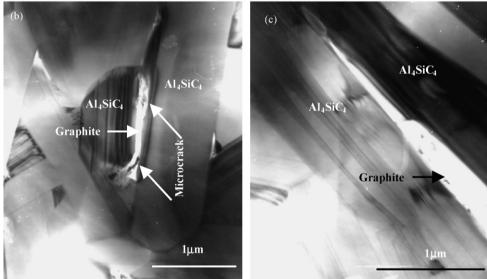


Fig. 4. TEM observations of Al<sub>4</sub>SiC<sub>4</sub>1700 ceramic. (a) Graphite phase with microcracks; (b) graphite phase with microcracks at the tip and (c) graphite phase as the weak interface.

which can be attributed to their weak interfacial bonding. The toughening by weak interfaces has been well documented in a number of materials [10-14] including graphite toughened B<sub>4</sub>C/TiC [13] and fibrous ceramic composites [14]. The low cracking resistance of interfaces in these materials was triggered by the layer structure of graphite which, on the application of stress, fractures readily along their basal plane [15,16]. In addition, there existed a large residual stress field related to the mismatch of the thermal expansion coefficients between graphite grains  $(2.5 \times 10^{-6} \text{ K}^{-1})$  [17] and Al<sub>4</sub>SiC<sub>4</sub> ceramics  $(6.2 \times 10^{-6} \text{ K}^{-1})$  [6]. The thermal expansion coefficient of Al<sub>4</sub>SiC<sub>4</sub> is much greater than that of graphite, which generates a compressive radial stress on the graphite grains, and a tensile hoop stress to the matrix. It is the interfacial stress that affects cracks, rendering the cracks propagate tortuously along the interfaces, thereby producing toughening effects.

# 3.3. High temperature bending strength of $Al_4SiC_4$ ceramics

The increased bending strength of  $Al_4SiC_4$  bulk ceramics from room temperature to  $1300~^{\circ}C$  in air can be seen in Table 1. For  $Al_4SiC_4$  bulk ceramics, at  $1000~^{\circ}C$ , the bending strength is 385 MPa, an increase of 30% over that at room temperature (300 MPa). Such strength value was maintained for the most part up to  $1200~^{\circ}C$ , followed by an anomalous gain in strength at  $1300~^{\circ}C$  with a very high value of 450 MPa, an increase of 50% over that at room temperature (300 MPa). In the authors' knowledge, it is a novel property that the bending strength of such material remains increasing up to  $1300~^{\circ}C$  in air.

Such increased strength is thought to be mainly related with the release of the residual thermal stress as mentioned above, with the same mechanism as occurs in graphite materials [18]. Another factor be considered is the crack-healing on the surface

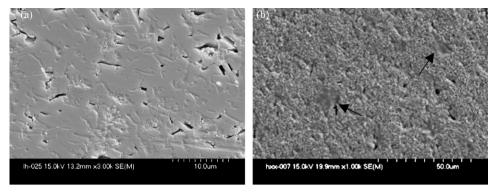


Fig. 5. Surface morphologies of the specimen after the high temperature bending testing. (a) 1000 °C and (b) 1300 °C in air.

of the specimens due to oxidation. Fig. 5(a and b) shows the SEM morphologies of the  $Al_4SiC_4$  specimen surface after bending test at 1000 and 1300 °C, respectively. From this figure we can see that there were a lot of narrow pores or cracks on the surface of the specimen tested at 1000 °C. Whereas, the self-healing of the flaws on the surface of the specimen was visible by the viscous flow of the glass due to oxidation at 1300 °C (labeled with arrows in Fig. 5(b)), which might be a new mechanism that was not present in graphite resulting in a large increase of the high temperature strength.

To verify the above hypothesis that the crack-healing played an important role on the higher temperature strength gain, a test of high temperature bending strength in vacuum was conducted at  $1300\,^{\circ}$ C. Fig. 6(a) shows the results of the bending strength in

air and in vacuum, respectively. The bending strength in vacuum (about 270 MPa), is almost the same than that at room temperature. The surface morphologies of  $Al_4SiC_4$  ceramics tested in air and in vacuum (Fig. 6(b and c)) were investigated, respectively. The specimen tested in air at  $1300\,^{\circ}C$  shows a rugous, glassy feature in the surface because of oxidation. X-ray and EDS analysis (not shown here) reveal that the oxidation layer is composed of  $Al_2O_3$  and amorphous oxide, of aluminosilicate glass. Differently, in vacuum condition, a number of large pores were observed in the tested specimen surface (Fig. 6(c)), which decreased the fracture stress more or less. So, it is reasonable to conclude that the enhanced mechanism in bending strength at high temperatures would be attributed to the self-healing behavior of the flaws in the surface

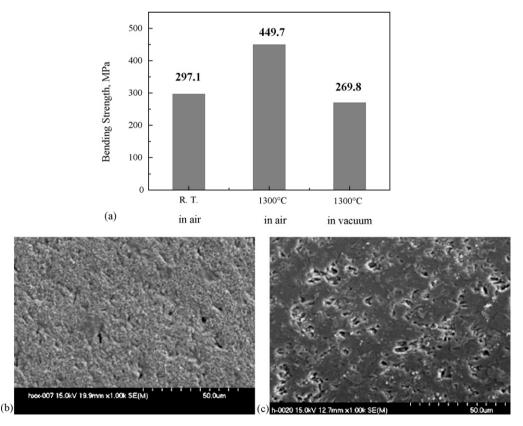


Fig. 6. Bending strengths tested at RT and high temperatures at different testing environments and corresponding surface morphologies observations of Al<sub>4</sub>SiC<sub>4</sub> ceramics. (a) Bending strengths, (b) tested at 1300 °C in air and (d) tested at 1300 °C in vacuum.

caused by oxidation similar to Mullite/SiC [19],  $Al_2O_3/SiC$  [20] and SiC [21].

### 4. Conclusions

Microstructure, mechanical properties and the corresponding enhanced mechanism of  $Al_4SiC_4$  ceramics in toughness at room temperature and in bending strength at higher temperatures in air were investigated. The toughening mechanism is caused by the weak interfaces and interfacial strain fields. At high temperatures, the bending strength of  $Al_4SiC_4$  ceramics increases with increasing test temperatures up to  $1300\,^{\circ}C$ . The strength value is  $450\,^{\circ}MPa$  at  $1300\,^{\circ}C$  in air, which was about 1.5 times of that at room temperature (300 MPa). The self-healing behavior of the flaws on the specimen surface due to the oxidation of the surface layer of the  $Al_4SiC_4$  ceramics is considered as the main enhancement mechanism at high temperatures.

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